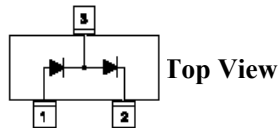
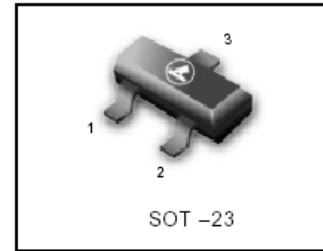


Dual In-Series Small-Signal Switching Diode

- Silicon Epitaxial Planar Diode
- Fast switching dual in-series diode, especially suited for applications requiring high voltage capability



LSD2004SLT1



Driver Marking

LSD2004SLT1 =DB6

Maximum Ratings and Thermal Characteristics

TA = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Continuous Reverse Voltage	VR	240	V
Peak Repetitive Reverse Voltage	VRRM	300	V
Peak Repetitive Reverse Current	IRRM	200	mA
Forward Current (continuous)	IF	225	mA
Peak Repetitive Forward Current	IRFM	625	mA
Non-Repetitive Peak Forward Current			
at tp = 1μs	IFSM	4	A
at tp = 1s		1	
Power Dissipation	Ptot	350	mW
Typical Thermal Resistance Junction to Ambient Air	RθJA	357	°C/W
Junction Temperature	Tj	150	°C
Storage Temperature Range	TS	-65 to +150	°C

Electrical Characteristics

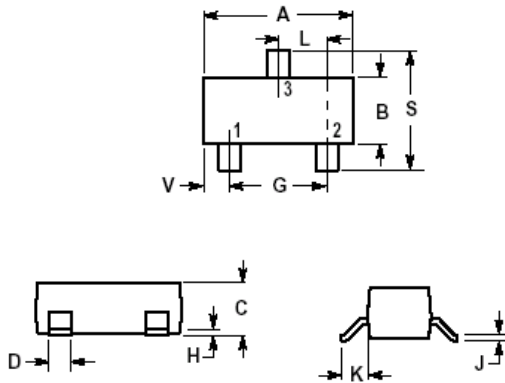
T_J = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse Breakdown Voltage	V _{BR}	I _R = 100μA	300	—	—	V
Leakage Current	I _R	V _R = 240V	—	—	100	nA
		V _R = 240V, T _j = 150°C	—	—	100	μA
Forward Voltage	V _F	I _F = 20mA	—	—	0.87	V
		I _F = 100mA	—	—	1	
Capacitance	C _{tot}	V _F =V _R =0	—	—	5	pF
		f=1MHz	—	—	5	pF
Reverse Recovery Time	t _{rr}	I _F =I _A =30mA	—	—	50	ns
		I _{rr} =30mA, R _L =100Ω	—	—	50	ns

SOT-23

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982
2. CONTROLLING DIMENSION: INCH



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

